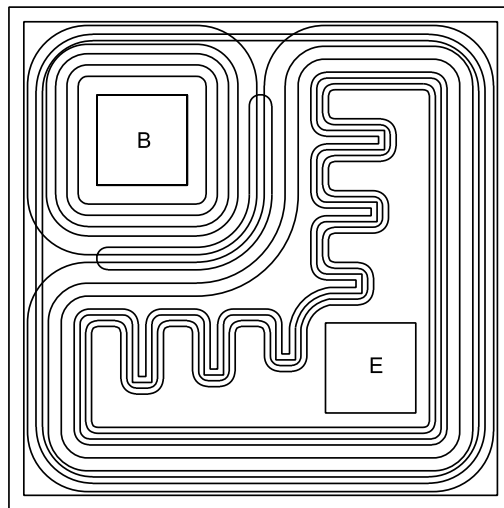


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	27 x 27 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	4.2 x 4.2 MILS
Emitter Bonding Pad Area	4.3 x 4.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 13,000Å

**GEOMETRY**



BACKSIDE COLLECTOR

R0

**GROSS DIE PER 4 INCH WAFER**

15,980

**PRINCIPAL DEVICE TYPES**

CMPTA29  
CZTA29  
MPSA29

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
www.centalsemi.com

R0 (20 -January 2006)